

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 52775-025		SERIAL NO. <div style="font-size: 1.5em; text-align: center;">10/665,483</div>	
				APPLICANT Masahiro NAKAYAMA, et al.			
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U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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						Yes	No
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
J.A.		"Thick Layer Growth of GaN by Hydride Vapor Phase Epitaxy", IEICE, C-II, vol. J81-C-II, No.1, pp58-64 (1998)	
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EXAMINER <div style="font-size: 1.2em; text-align: center;">Jacob Adam Jr.</div>	DATE CONSIDERED <div style="font-size: 1.2em; text-align: center;">11/30/04</div>
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